



LGE3D30090H

Silicon Carbide Schottky Diode



General Description

This product family offers state of the art performance. It is designed for high frequency applications here high efficiency and high reliability are required.

V_{RRM}	= 100 90	V
$I_F (T_C \leq 140^\circ C)$	= 10 30	A
Q_C	= 100 10	nC

Features

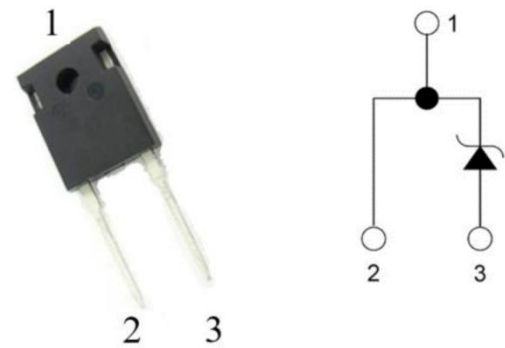
- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior
- High surge current capability

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

Applications

- Motor Drives
- Solar/Wind Inverters
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies



TO-247-2

Key performance parameters

Type	V_R	I_F $T_C=140^\circ C$	Q_C
LGE3D30090H	900V	30A	101nC

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.



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Maximum Ratings

$T_C=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	900	V

Maximum Ratings

$T_C=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous Forward Current: $T_C = 25^{\circ}\text{C}$ $T_C = 130^{\circ}\text{C}$ $T_C = 140^{\circ}\text{C}$	I_F	69 35 30	A
Non Repetitive Forward Surge Current $T_C = 25^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse $T_C = 110^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse	I_{FSM}	180 165	A
Repetitive peak Forward Surge Current Freq = 0.1Hz, 100 cycles $T_C = 25^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse $T_C = 110^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Pulse	I_{FRM}	170 155	A
Total power dissipation : $T_C = 25^{\circ}\text{C}$ $T_C = 110^{\circ}\text{C}$	P_D	250 87	W
Single Pulse Avalanche Energy: $L=2\text{mH}$, $I_{AS}=13\text{A}$	E_{AS}	169	mJ
Diode dv/dt ruggedness: $V_R=0-900\text{v}$	dv/dt	80	V/ns
Operating Junction Temperature:	T_J	-55 to 175	$^{\circ}\text{C}$
Storage Temperature :	T_{stg}	-55 to 175	$^{\circ}\text{C}$

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Thermal Resistance

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, junction-case	$R_{th(j-c)}$	0.6		$^{\circ}C/W$

Electrical Characteristic

$T_C = 25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
DC Blocking Voltage	V_{DC}	900			V	$T_J = 25^{\circ}C$
Forward Voltage	V_F		1.45 1.71 1.91	1.75	V	$I_F = 30A$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$ $T_J = 175^{\circ}C$
Reverse Current	I_R		5 28 85	150	μA	$V_R = 900V$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$ $T_J = 175^{\circ}C$
Total Capacitance Charge	Q_C		101		nC	$V_R = 600V, T_J = 25^{\circ}C$
Total Capacitance	C		1350 125 105		pF	$T_J = 25^{\circ}C, F_{req} = 1MHz$ $V_R = 1V$ $V_R = 300V$ $V_R = 600V$
Note: This is a majority carrier diode, so there is no reverse recovery charge						

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Characteristics Curves

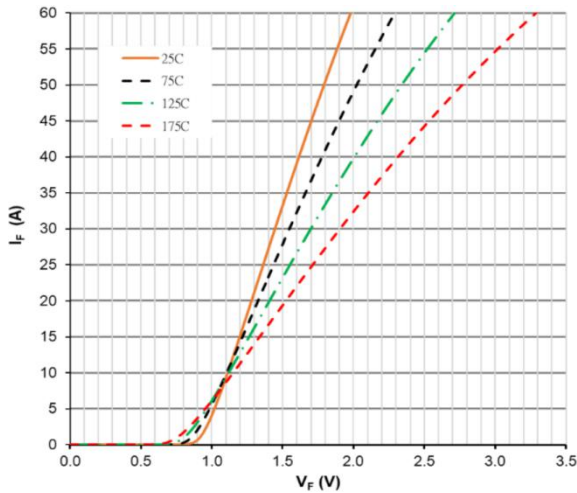


Figure 1. Forward Characteristics

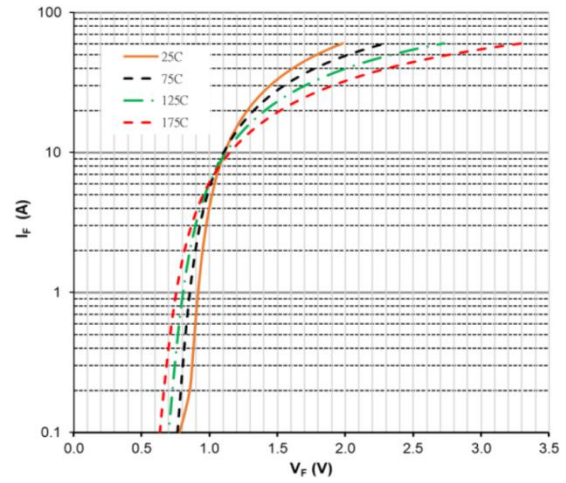


Figure 2. Forward Characteristics

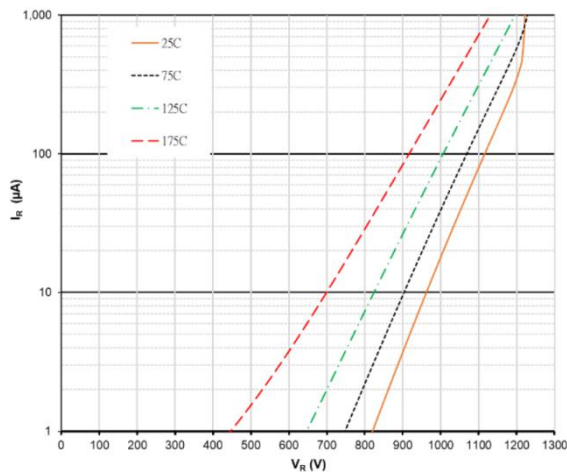


Figure 3. Reverse Characteristics

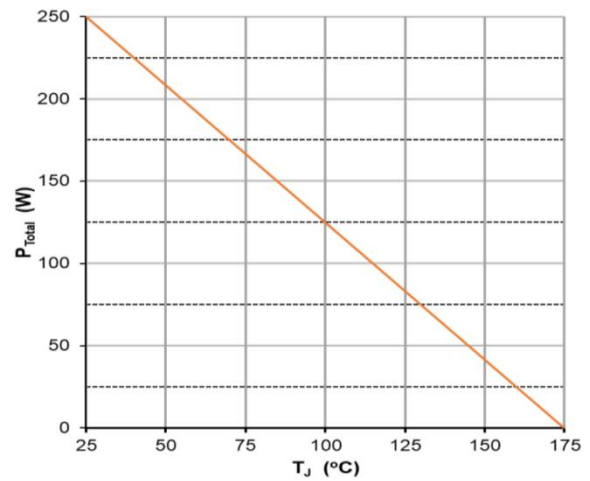


Figure 4. Power Derating

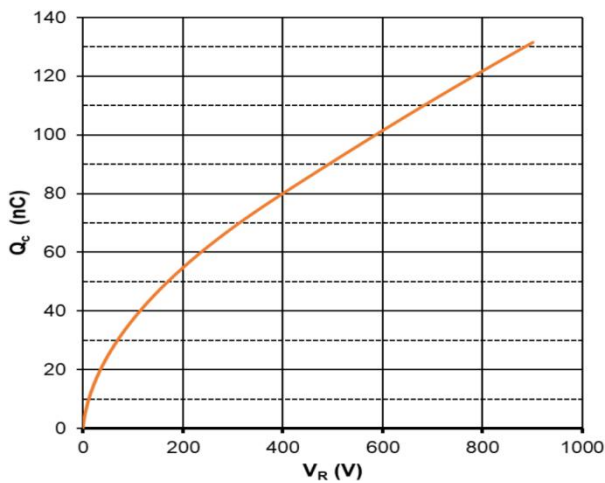


Figure 5. Reverse charge vs Reverse Voltage

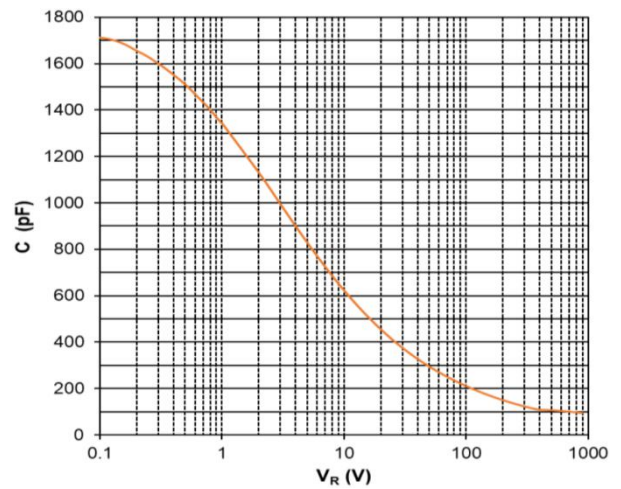


Figure 6. Capacitance vs. Reverse Voltage

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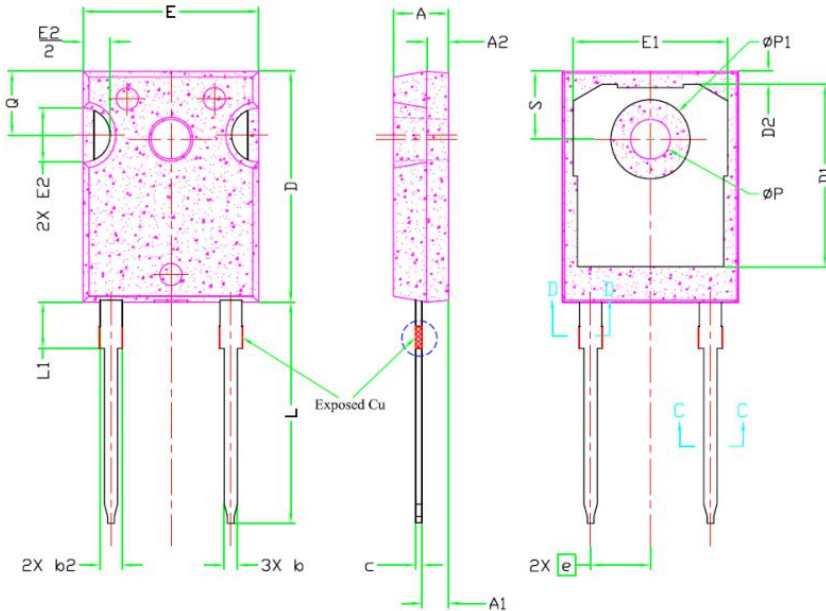


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Package Dimensions: (TO-247-2 Package)

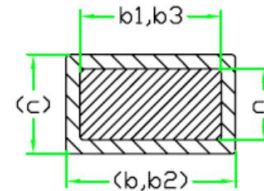


SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	



Note:

1. Package Reference: JEDEC TO247, Variation AD.
2. All Dimensions Are In mm.
3. Slot Required, Notch May Be Rounded
4. Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
5. Thermal Pad Contour Optional Within Dimension D1 & E1.
6. Lead Finish Uncontrolled In L1.
7. ØP To Have A Maximum Draft Angle Of 1.5° To The Top Of The Part With A Maximum Hole Diameter Of 3.91mm.
8. Dimension "b2" And "b4" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.10mm Total In Excess Of "b2" And "b4" Dimension At Maximum Material Condition.



Section C-C, D-D

Package	Packing	Box Size LxWxH(mm)	Quantity(pcs/box)	Carton Size LxWxH(mm)	Quantity(pcs/carton)
TO-247	30pcs/Tube	570x155x50	450	580x340x125	1800

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